

**Texas A&M University
Department of Electrical and Computer Engineering**

ECEN 325 – Electronics

Spring 2020

Exam #3

Instructor: Sam Palermo

- Please write your name in the space provided below
- Please verify that there are 5 pages in your exam
- You may use one double-sided page of notes and equations for the exam
- Good Luck!

Problem	Score	Max Score
1		50
2		50
Total		100

Name: SAM PALERMO

UIN: _____

Problem 1 (50 points)

For all the circuits below, use the following NMOS parameters

$$K_{PN} = \mu_n C_{ox} = 100 \mu A/V^2, V_{TN} = 1V, \lambda_N = 0V^{-1}$$

and the following PMOS parameters

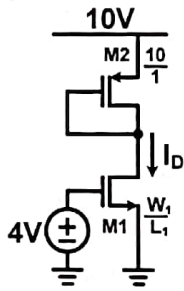
$$K_{PP} = \mu_p C_{ox} = 30 \mu A/V^2, V_{TP} = -1V, \lambda_P = 0V^{-1}$$

For the following two circuits calculate

i. I_D with $W_1/L_1 = 10/1$. (15 points)

ii. The maximum W_1/L_1 such that the M1 transistor remains in saturation (15 points)

a)



For M1 Sat: $V_{DS1} \geq V_{GS1} - V_{TN} \Rightarrow V_{D1} \geq 4V - 1V = 3V$

$$I_D = \frac{100 \mu}{2} (10) (3V)^2 = 4.5 mA$$

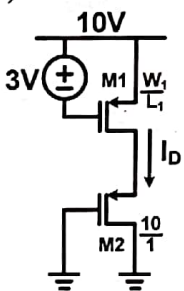
$$V_{D1} = 10V - \left(\sqrt{\frac{2(4.5mA)}{30 \mu (10)}} + |-1V| \right) = 3.52V \Rightarrow M1 \text{ Sat}$$

$$\text{Max } \left(\frac{W}{L}\right)_1 = \frac{2I_D}{K_{PN} (V_{GS1} - V_{TN})^2} \text{ where } I_D = \frac{1}{2} K_{PP} \left(\frac{W}{L}\right)_2 (V_{SG2} - |V_{TP}|)^2$$

$$= \frac{2 \left(\frac{K_{PP}}{2}\right) \left(\frac{W}{L}\right)_2 (V_{SG2} - |V_{TP}|)^2}{K_{PN} (V_{GS1} - V_{TN})^2} = \frac{K_{PP} \left(\frac{W}{L}\right)_2 (V_{SG2} - |V_{TP}|)^2}{K_{PN} (V_{GS1} - V_{TN})^2} = \frac{30 \mu (10) (7-1)^2}{100 \mu (4-1)^2} = 12$$

$I_D (W_1/L_1 = 10/1) = 4.5 mA$

b)



For M1 Sat: $V_{SD1} \geq V_{SG1} - |V_{TP}|$ M1 Sat. Max $W_1/L_1 = 12$

$$V_{SD1} \geq 3V - |-1V| = 2V \Rightarrow V_{D1} \leq 8V$$

$$I_D = \frac{30 \mu}{2} (10) (2V)^2 = 600 \mu A$$

$$V_{D1} = \sqrt{\frac{2(600 \mu)}{30 \mu (10)}} + |-1V| = 3V \Rightarrow M1 \text{ Sat}$$

$$\text{Max } \left(\frac{W}{L}\right)_1 = \frac{2I_D}{K_{PP} (V_{SG1} - |V_{TP}|)^2} \text{ where } I_D = \frac{1}{2} K_{PP} \left(\frac{W}{L}\right)_2 (V_{SG2} - |V_{TP}|)^2$$

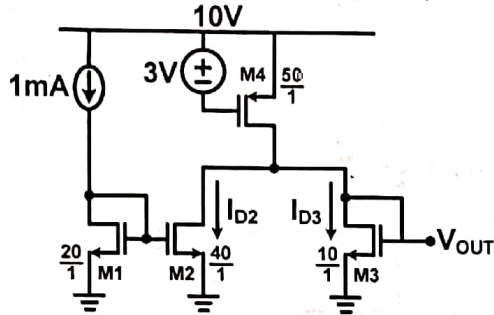
$$= \frac{2 \left(\frac{K_{PP}}{2}\right) \left(\frac{W}{L}\right)_2 (V_{SG2} - |V_{TP}|)^2}{K_{PP} (V_{SG1} - |V_{TP}|)^2} = \frac{\left(\frac{W}{L}\right)_2 (V_{SG2} - |V_{TP}|)^2}{(V_{SG1} - |V_{TP}|)^2}$$

$I_D (W_1/L_1 = 10/1) = 600 \mu A$

M1 Sat. Max $W_1/L_1 = 122.5$

$$= \frac{10 (8-1)^2}{(3-1)^2} = 122.5$$

c) For the following circuit find the values for I_{D2} , I_{D3} , and V_{OUT} . Assume all transistors are operating in saturation. (20 points)



From current mirror ($M1/M2$)

$$I_{D2} = 1mA \left(\frac{40/1}{20/1} \right) = 2mA$$

$$I_{D2} = 2mA$$

$$I_{D3} = 1mA$$

$$V_{OUT} = 2.41V$$

$$I_{D4} = \frac{1}{2} K_P \left(\frac{W}{L} \right)_4 (V_{GS4} - |V_{TP}|)^2 = \frac{30\mu}{2} (50) (3V - (-1V))^2 = 3mA$$

$$I_{D3} = I_{D4} - I_{D2} = 3mA - 2mA = 1mA$$

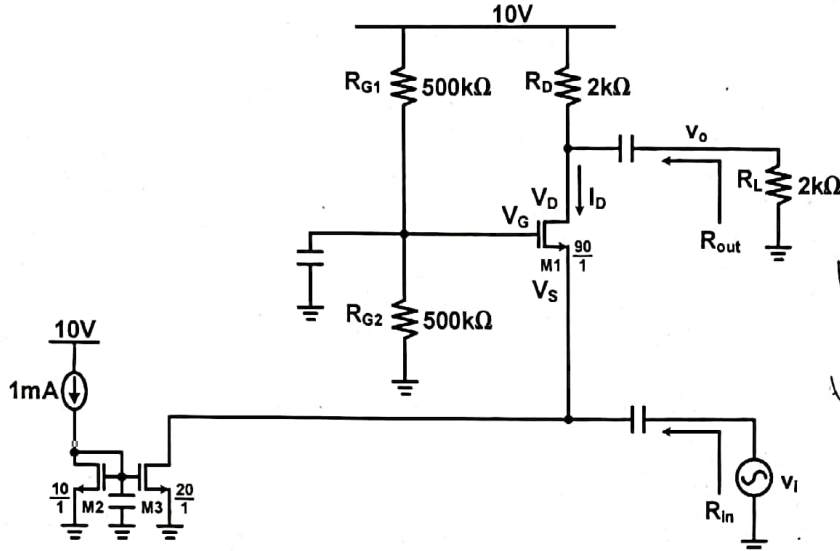
$$V_{OUT} = \sqrt{\frac{2I_{D3}}{K_P \left(\frac{W}{L} \right)_3}} + V_{TN} = \sqrt{\frac{2(1mA)}{k_{n\mu}(10)}} + 1 = 2.41V$$

Problem 2 (50 points)

Assume for problem 2 that the NMOS transistors are all operating in saturation and have

$$K_{PN} = \mu_n C_{ox} = 100 \mu A/V^2, V_{TN} = 1V, \lambda_N = 0V^{-1}$$

a) Calculate the DC values for I_D , V_D , V_G , V_S and the AC small-signal g_{m1} . (15 points)



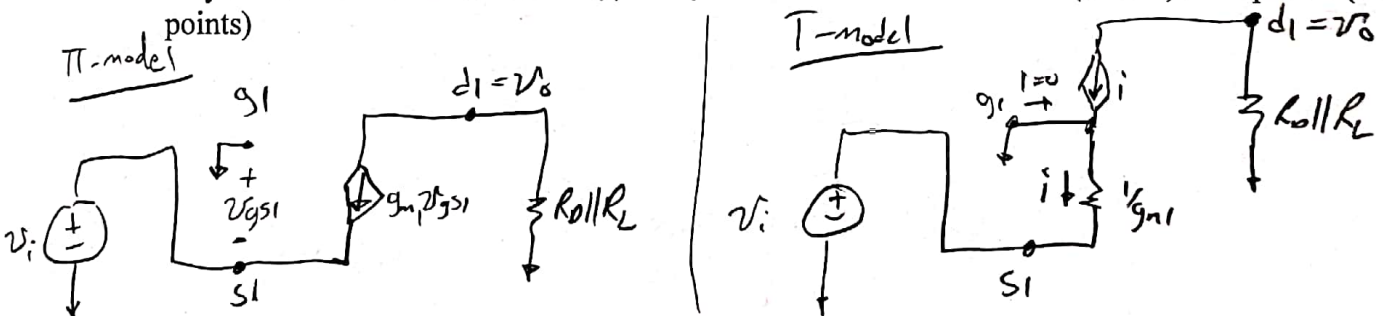
From current mirror
 $I_D = 1mA \left(\frac{20\Omega}{10\Omega} \right) = 2mA$
 $V_G = 10V \left(\frac{500k}{500k+500k} \right) = 5V$
 $V_D = 10V - 2mA(2k) = 6V$

$$V_S = V_G - (V_{DS1} + V_{TN}) = 5V - \left(\sqrt{\frac{2(2mA)}{100\mu A/V^2}} + 1 \right) = 3.33V$$

$$g_{m1} = \sqrt{K_{PN} \left(\frac{W}{L} \right) 2I_D} = \sqrt{100\mu A/V^2 (10) (2) (2mA)} = 6 mA/V$$

- $I_D = 2mA$
- $V_D = 6V$
- $V_G = 5V$
- $V_S = 3.33V$
- $g_{m1} = 6 mA/V$

b) Sketch the small-signal model of the circuit. Assume that the capacitors act as AC shorts and only draw the essential transistor(s). Only ONE version of the model (π or T) is required. (15 points)



c) Calculate small signal gain $A_v = v_o/v_i$, input resistance R_{in} , output resistance R_{out} . (20 points)

From π -model $\Rightarrow v_{gs1} = -v_{in}$
 $v_o = -g_{m1} v_{gs1} (R_D || R_L) = g_{m1} v_{in} (R_D || R_L)$
 $A_v = \frac{v_o}{v_i} = g_{m1} (R_D || R_L) = 6 mA/V (2k || 2k) = 6V/V$
 $R_{in} = \frac{v_{in}}{i_{in}} = \frac{v_{in}}{-(-g_{m1} v_{in})} = \frac{1}{g_{m1}} = 167 \Omega$

- $A_v = 6 V/V$
- $R_{in} = 167 \Omega$
- $R_{out} = 2k \Omega$

